

# MJD122 (NPN) MJD127 (PNP)

Preferred Device

## Complementary Darlington Power Transistor

### DKPAK For Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

#### Features

- Pb-Free Packages are Available
- Lead Formed for Surface Mount Applications in Plastic Sleeves
- Available in 16 mm Tape and Reel ("T4" Suffix)
- Surface Mount Replacements for 2N6040–2N6045 Series, TIP120–TIP122 Series, and TIP125–TIP127 Series
- Monolithic Construction With Built-in Base-Emitter Shunt Resistors
- High DC Current Gain –  
 $h_{FE} = 2500$  (Typ) @  $I_C = 4.0$  Adc
- Epoxy Meets UL 94, V-0 @ 0.125 in.
- ESD Ratings: Human Body Model, 3B > 8000 V  
Machine Model, C > 400 V

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	100	Vdc
Collector-Base Voltage	$V_{CB}$	100	Vdc
Emitter-Base Voltage	$V_{EB}$	5	Vdc
Collector Current – Continuous Peak	$I_C$	8 16	Adc
Base Current	$I_B$	120	mAdc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	20 0.16	W W/ $^\circ\text{C}$
Total Power Dissipation* @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.75 0.014	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	6.25	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient*	$R_{\theta JA}$	71.4	$^\circ\text{C}/\text{W}$

\*These ratings are applicable when surface mounted on the minimum pad sizes recommended.

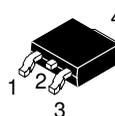


ON Semiconductor®

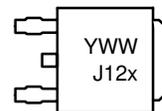
<http://onsemi.com>

**SILICON  
POWER TRANSISTOR  
8 AMPERES  
100 VOLTS  
20 WATTS**

#### MARKING DIAGRAM



DKPAK  
CASE 369C  
STYLE 1



Y = Year  
WW = Work Week  
x = 2 or 7

#### ORDERING INFORMATION

Device	Package	Shipping†
MJD122	DKPAK	75 Units/Rail
MJD122T4	DKPAK	2500/Tape & Reel
MJD122T4G	DKPAK (Pb-Free)	2500/Tape & Reel
MJD127	DKPAK	75 Units/Rail
MJD127G	DKPAK (Pb-Free)	75 Units/Rail
MJD127T4	DKPAK	2500/Tape & Reel
MJD127T4G	DKPAK (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

# MJD122 (NPN)

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

### OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage ( $I_C = 30\text{ mA}$ , $I_B = 0$ )	$V_{CE(sus)}$	100	–	Vdc
Collector Cutoff Current ( $V_{CE} = 50\text{ Vdc}$ , $I_B = 0$ )	$I_{CEO}$	–	10	$\mu\text{A}$
Collector Cutoff Current ( $V_{CB} = 100\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	–	10	$\mu\text{A}$
Emitter Cutoff Current ( $V_{BE} = 5\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	2	$\text{mA}$

### ON CHARACTERISTICS

DC Current Gain ( $I_C = 4\text{ A}$ , $V_{CE} = 4\text{ Vdc}$ ) ( $I_C = 8\text{ A}$ , $V_{CE} = 4\text{ Vdc}$ )	$h_{FE}$	1000 100	12,000 –	–
Collector–Emitter Saturation Voltage ( $I_C = 4\text{ A}$ , $I_B = 16\text{ mA}$ ) ( $I_C = 8\text{ A}$ , $I_B = 80\text{ mA}$ )	$V_{CE(sat)}$	– –	2 4	Vdc
Base–Emitter Saturation Voltage (Note 1) ( $I_C = 8\text{ A}$ , $I_B = 80\text{ mA}$ )	$V_{BE(sat)}$	–	4.5	Vdc
Base–Emitter On Voltage ( $I_C = 4\text{ A}$ , $V_{CE} = 4\text{ Vdc}$ )	$V_{BE(on)}$	–	2.8	Vdc

### DYNAMIC CHARACTERISTICS

Current–Gain–Bandwidth Product ( $I_C = 3\text{ A}$ , $V_{CE} = 4\text{ Vdc}$ , $f = 1\text{ MHz}$ )	$ h_{fe} $	4	–	MHz
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 0.1\text{ MHz}$ )	$C_{ob}$	– –	300 200	pF
Small–Signal Current Gain ( $I_C = 3\text{ A}$ , $V_{CE} = 4\text{ Vdc}$ , $f = 1\text{ kHz}$ )	$h_{fe}$	300	–	–

1. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

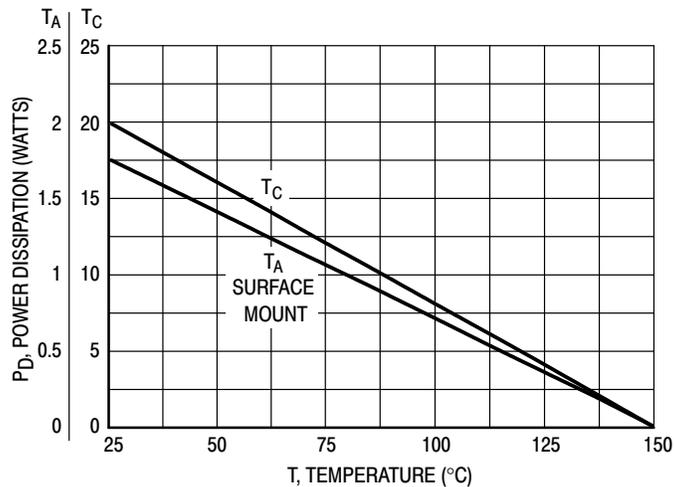


Figure 1. Power Derating

# MJD122 (NPN)

## TYPICAL ELECTRICAL CHARACTERISTICS

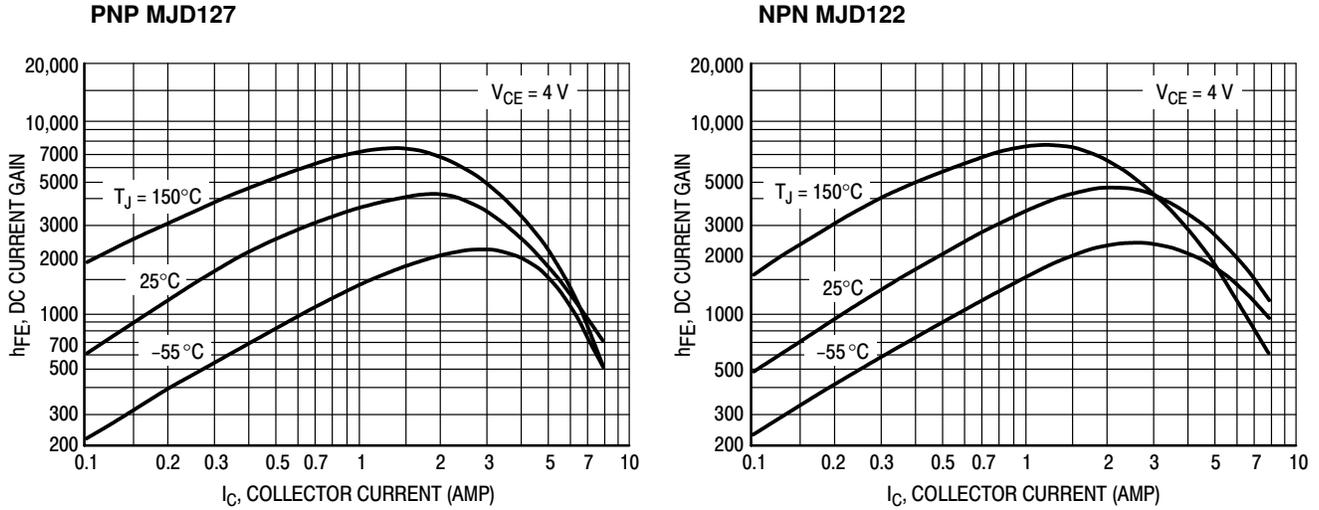


Figure 2. DC Current Gain

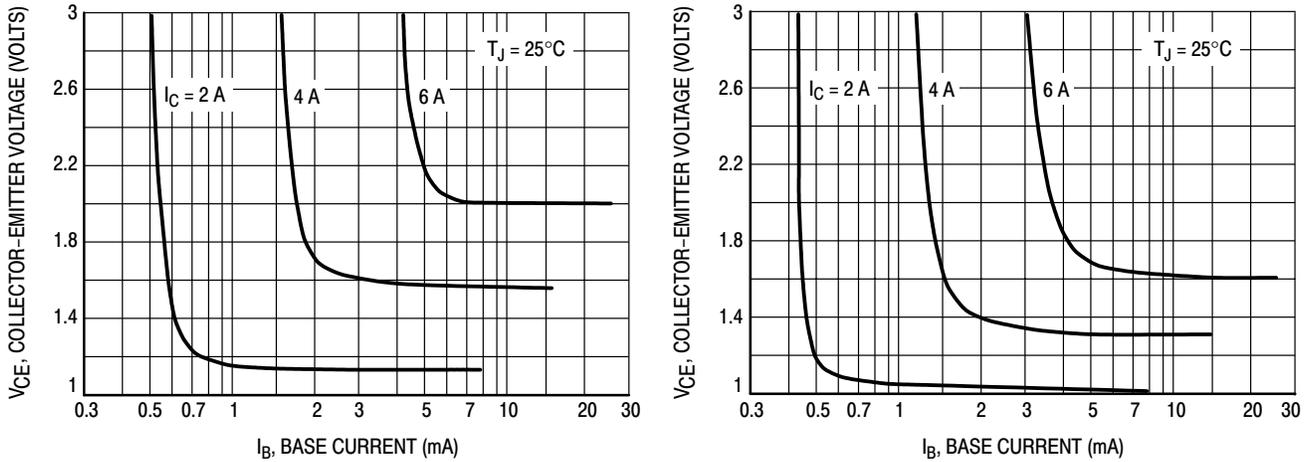


Figure 3. Collector Saturation Region

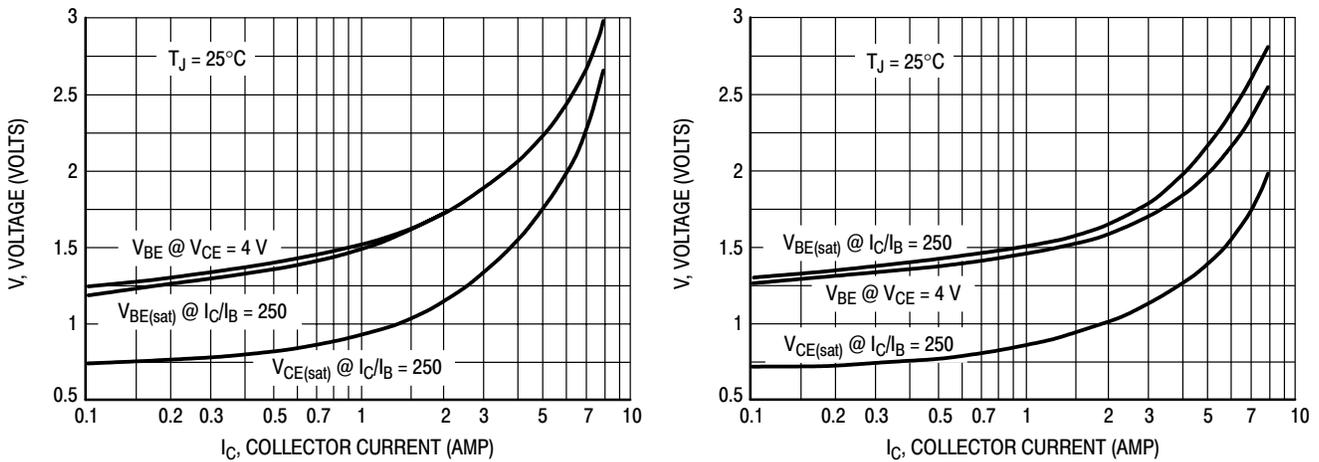


Figure 4. "On" Voltages

# MJD122 (NPN)

## TYPICAL ELECTRICAL CHARACTERISTICS

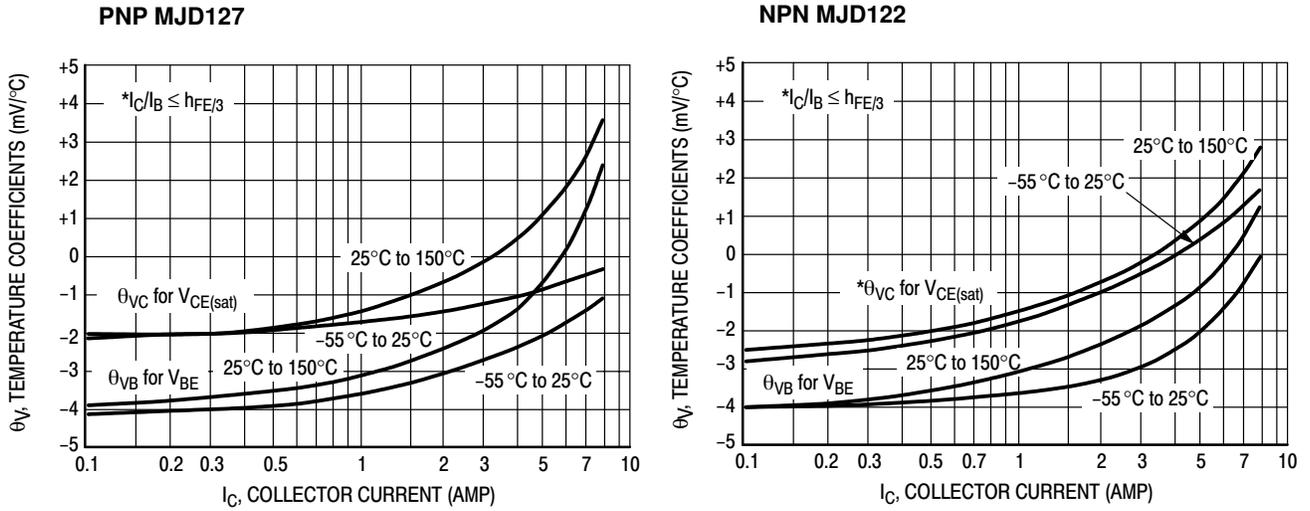


Figure 5. Temperature Coefficients

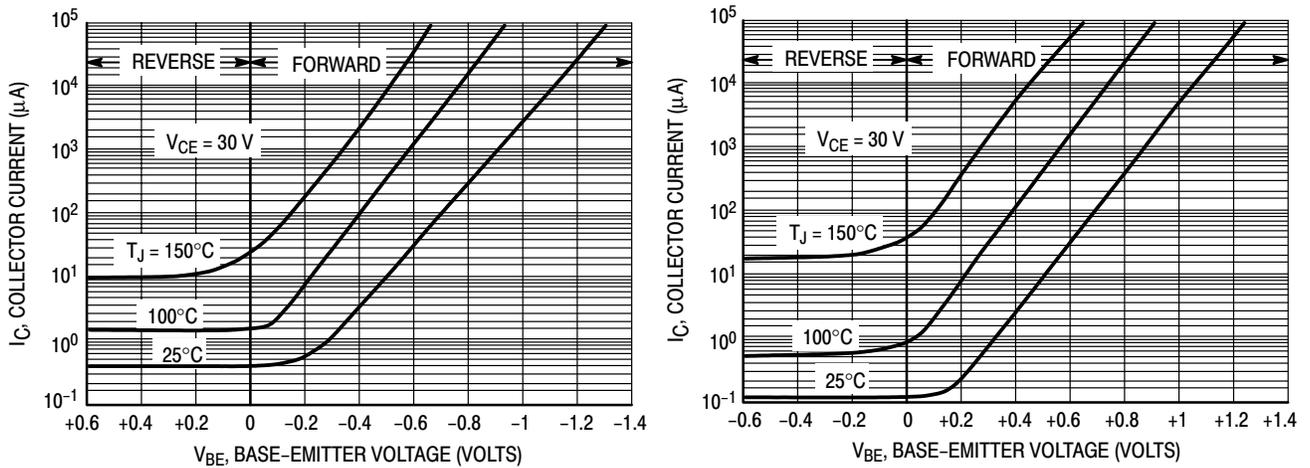


Figure 6. Collector Cut-Off Region

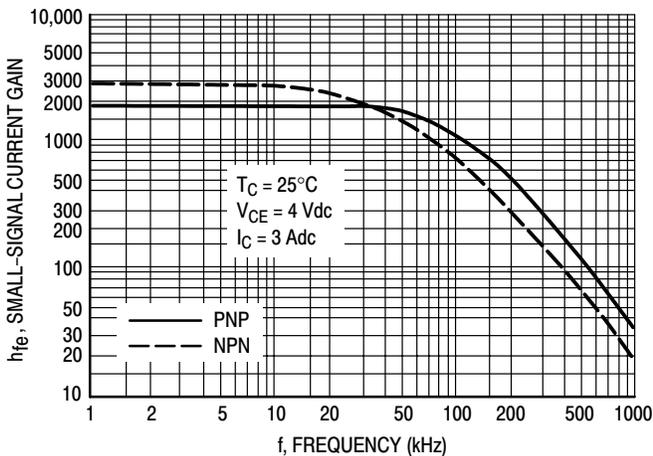


Figure 7. Small-Signal Current Gain

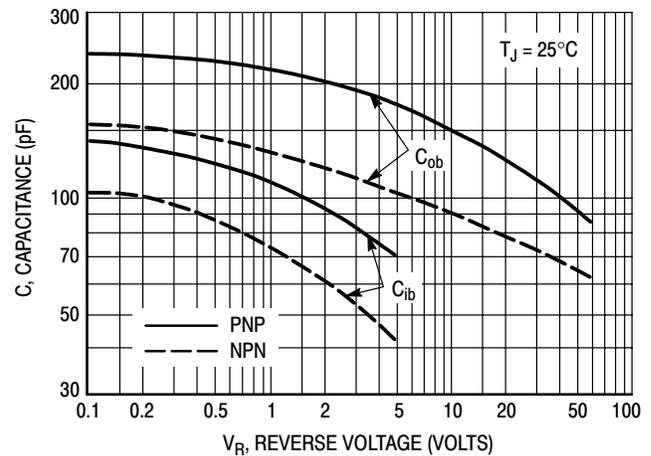


Figure 8. Capacitance

# MJD122 (NPN)

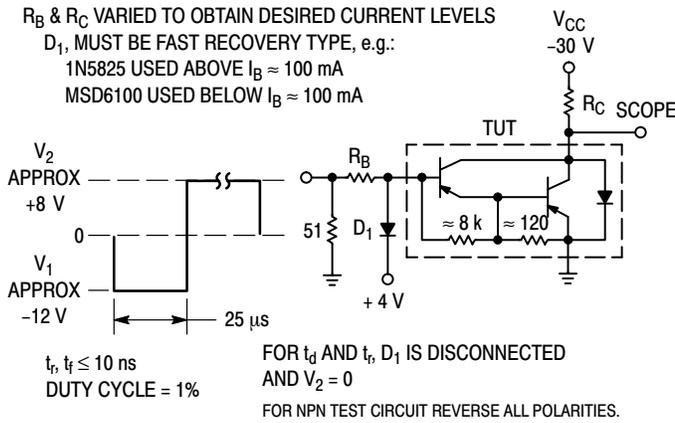


Figure 9. Switching Times Test Circuit

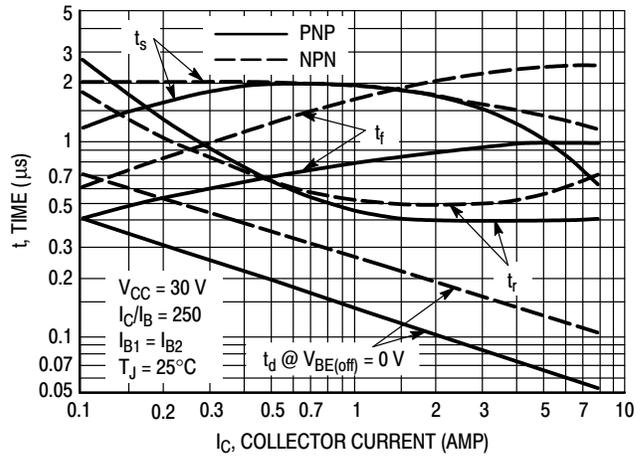


Figure 10. Switching Times

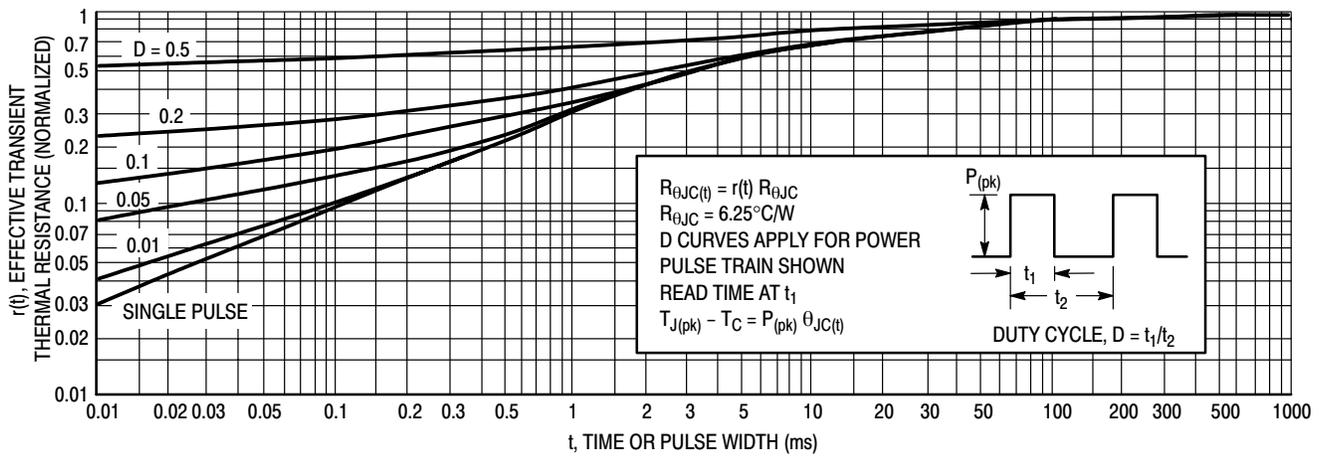


Figure 11. Thermal Response

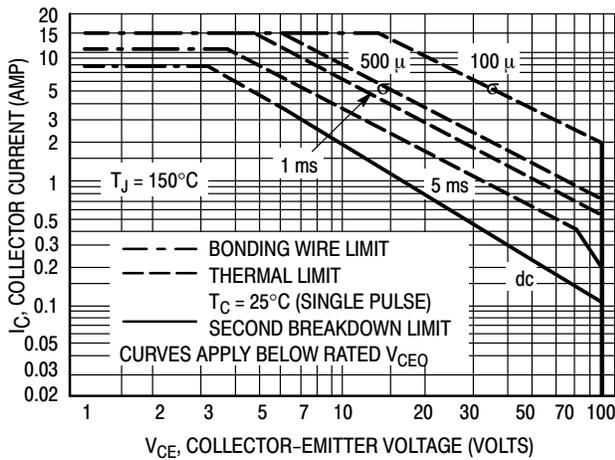


Figure 12. Maximum Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 12 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 11. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

# MJD122 (NPN)

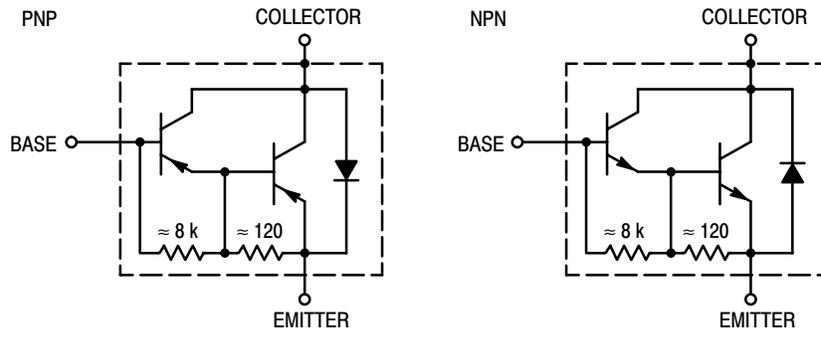
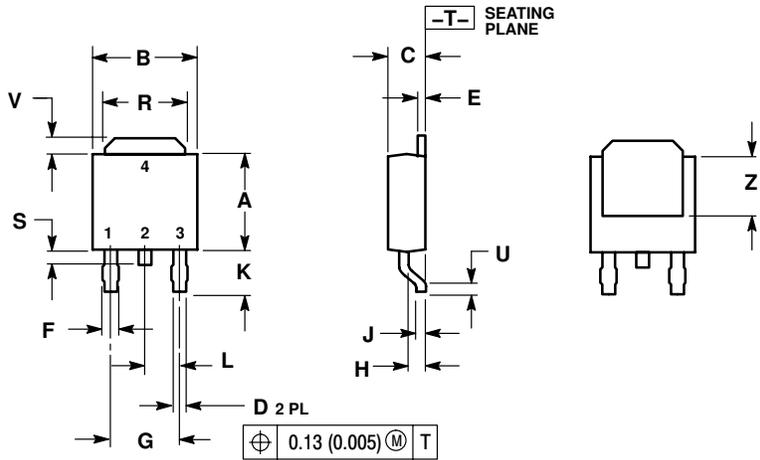


Figure 13. Darlington Schematic

# MJD122 (NPN)

## PACKAGE DIMENSIONS

DPAK  
CASE 369C-01  
ISSUE O

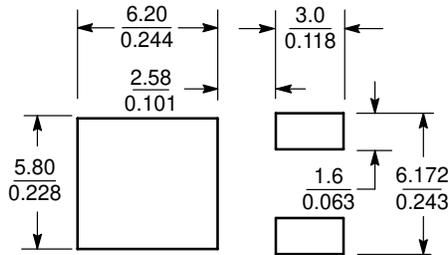


- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

## SOLDERING FOOTPRINT\*



SCALE 3:1  $\left(\frac{\text{mm}}{\text{inches}}\right)$

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MJD122 (NPN)

**ON Semiconductor** and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
P.O. Box 61312, Phoenix, Arizona 85082-1312 USA

**Phone:** 480-829-7710 or 800-344-3860 Toll Free USA/Canada

**Fax:** 480-829-7709 or 800-344-3867 Toll Free USA/Canada

**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada

**Japan:** ON Semiconductor, Japan Customer Focus Center  
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051  
**Phone:** 81-3-5773-3850

**ON Semiconductor Website:** <http://onsemi.com>

**Order Literature:** <http://www.onsemi.com/litorder>

For additional information, please contact your  
local Sales Representative.

This datasheet has been download from:

[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.